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Enhanced resonance frequency in Co₂FeAl thin film with different thicknesses grown on flexible graphene substrate*

Cai Zhou(周偲),^{1,3} Shaokang Yuan(袁少康),^{2,3} Dengyu Zhu(朱登玉),^{2,3} Yuming Bai(白宇明),⁴ Tao Wang(王韬),⁴ Fufu Liu(刘福福),⁵ Lulu Pan(潘禄禄),⁶ Cunfang Feng(冯存芳),^{1,3} Bohan Zhang(张博涵),^{1,3,†} Daping He(何大平)⁷ and Shengxiang Wang(汪胜祥)^{1,3,*}

¹ Hubei Engineering and Technology Research Center for Functional Fiber Fabrication and Testing, Wuhan Textile University, Wuhan 430200, P. R. China

² School of Electronic and Electrical Engineering, Wuhan Textile University, Wuhan 430200, P. R. China

³ School of Mathematical and Physical Sciences, Wuhan Textile University, Wuhan 430200, P. R. China

⁴ School of Integrated Circuits, Huazhong University of Science and Technology, Wuhan 430074, P. R. China

⁵ Key Laboratory for Magnetism and Magnetic Materials, Ministry of Education, Lanzhou University, Lanzhou 730000, P. R. China

⁶ Beijing National Center for Condensed Matter Physics and Institute of Physics, Chinese Academy of Sciences, Beijing 100190, P. R. China

⁷ Hubei Engineering Research Center of RF-Microwave Technology and Application, Wuhan University of Technology, Wuhan 430070, P. R. China

The flexible materials exhibit more favorable properties than most rigid substrates in flexibility, weight saving, mechanical reliability, and excellent environmental toughness. Particularly, flexible graphene film with unique mechanical properties extensively explored in high frequency devices. Herein, we report the characteristics of structure and magnetic property at high frequency of Co₂FeAl thin film with different thicknesses grown on flexible graphene substrate at room temperature. The exciting finding for columnar structure of Co₂FeAl thin film laid the foundation of excellent high frequency property of Co₂FeAl/flexible graphene structure. In-plane magnetic anisotropy field varying with increasing thickness of Co₂FeAl thin film can be obtained by measurement of ferromagnetic resonance, which can be ascribed to enhancement of crystallinity and increase of grain size. Meanwhile, the resonance frequency which can be achieved by measurement of vector network analyzer with the microstrip method increase with increasing thickness of Co₂FeAl thin film. Moreover, in our case with graphene film, the resonance magnetic field is quite stable though folded it twenty cycles, which demonstrates that good flexibility of graphene film and the stability of high frequency magnetic property of Co₂FeAl thin film grown on flexible graphene substrate. These results are promising for the design of microwave devices and wireless communication equipment.

Keywords: Enhanced resonance frequency, Magnetic resonance field, flexible graphene substrate

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† Corresponding author. E-mail: bhzhang@wtu.edu.cn

* Corresponding author. E-mail: shxwang@wtu.edu.cn

42 **1. Introduction**

43 Recently, with improvement in the standard of living, the flexible electronic devices have received
44 wide attention owing to perfect stretchability, low cost, biocompatibility, and light weight, which have
45 great potential in application of sensitive skin, flexible circuit boards, and paper-like displays. In these
46 flexible materials, the advanced carbon material-based films, including carbon fibers,^[1] carbon
47 nanotubes,^[2-4] multi-shelled fullerenes,^[5,6] and especially graphene,^[7,8] exhibit more favorable
48 properties than most rigid substrates in flexibility, weight saving, mechanical reliability, and excellent
49 environmental toughness. The flexible graphene films can be extensively explored in high frequency
50 devices due to the unique mechanical properties.^[9-11] He's group has reported flexible graphene films
51 for radio-frequency antennas, multi-beam radiation, highly sensitive wearable sensor, etc.^[12-14] In fact,
52 the graphene film as flexible substrate is expected to Heusler metallic materials are considered to be
53 ideal compounds as high spin polarized current sources, and some of them generally have a high Currie
54 temperature, high spin polarization and low damping,^[15,16] Among the Heusler metallic materials, with
55 the formula of X₂YZ (where X is a transition metal element, Y is another transition metal element, and
56 Z is a main group sp element), particularly Co₂FeAl (CFA), have attracted intense research interest due
57 to the half-metals even at room temperature.^[17-19] Belmeguenai's research group have investigated the
58 static and dynamic magnetic property in CFA thin films by sputtering on a Si and MgO substrates
59 annealed at different temperatures.^[20] Our group have reported the electric field tuning magnetic
60 anisotropy in CFA thin film grown on PMN-PT substrate.^[21,22] In these cases, the CFA thin film were
61 fabricated on the above conventional rigid substrate. This greatly limits the application scope of
62 flexible thin film materials. Therefore, it is essential to study the magnetic properties of magnetic thin
63 films fabricated on flexible substrate. In this work, the high frequency property of CFA thin film with
64 different thicknesses grown on flexible graphene substrate (FGS) is analyzed in detail at room
65 temperature. With the thickness of CFA thin film grown on FGS varying from 20 nm to 200 nm, the
66 increase of grain size can be obtained. The in-plane magnetic anisotropy field decreases with increasing
67 the thickness of CFA thin film from 20 nm to 100 nm measured by ferromagnetic resonance, which can
68 be attributed to the change of structure of CFA thin film with different thicknesses grown on FGS.
69 However, in-plane magnetic anisotropy field increases with continuing to increase thickness to 200 nm,
70 which can lead to the resonance frequency shifting to higher frequency measured by using a vector
71 network analyzer with the microstrip method.

72

73 **2. Experimental details**

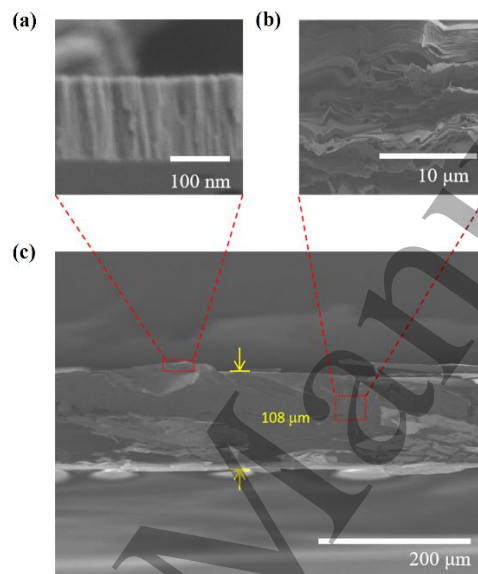
74 The CFA thin films with different thicknesses (20, 50, 100, 150, and 200 nm) were deposited by Direct
75 Current (DC) magnetron sputtering on FGS at a common base pressure $< 8 \times 10^{-4}$ Pa and work
76 processing Ar pressure of 0.1 Pa, a power of 150 W. A field emission scanning electron microscope
77 (SEM, Hitachi SU5000) was employed to observe the cross-section microstructures and the surface
78 morphologies. The x-ray diffraction (XRD) measurements were performed on X'Pert x-ray powder
79 diffractometer with CuK_α radiation (1.54056Å). The ferromagnetic resonance (FMR) measurements
80 were carried out with a PNA 8722ES vector network analyzer using the coplanar waveguide method.
81 Permeability spectra were carried out with a PNA E8363B vector network analyzer using the
82 microstrip method.

83

84 **3. Results and discussion**

85 The cross-sectional and highly magnified SEM images of the FGS show that the film based on orderly

86 stacked graphene layers with a thickness of 108 μm as shown in Fig. 1(b) and Fig. 1(c). The
87 cross-section image of CFA thin film with different thicknesses grown on FGS is also observed by
88 SEM. For brevity, only the 200 nm-thick CFA grown on FGS is shown in Fig. 1(a). The columnar
89 structure of CFA can be obviously observed, which is comparable to the sample grown on Si substrate.
90 [23,24] The exciting finding laid the foundation of the good quality of CFA/FGS structure. In addition,
91 surface morphologies of CFA/FGS structure with various thickness were shown in the inset of Fig. 2(b).
92 Firstly, the smooth surface morphologies of FGS can be obtained as shown in the top inset of Fig. 2(b).
93 Then, we can observe that with increasing thickness of CFA thin film, the grain continues growth and
94 corresponding size becomes larger. This result indicates thickness has a great influence on
95 microstructure for CFA thin film grown on FGS.



96
97 **Fig. 1.** The SEM cross-section images of (a) CFA thin film, (b) FGS and (c)CFA/FGS structure, respectively.

98
99 A piece of rolled FGS was shown in the inset of Fig. 2(a), which demonstrates FGS have good
100 flexibility. The crystal structures for all thin films were measured by XRD as shown in Fig. 2(a).The
101 sharp diffraction peak (002) and peak (004) of FGS is located at 26.3 $^\circ$ and 54.5 $^\circ$. The (022) peak of
102 CFA thin film appears at 44.7 $^\circ$. Moreover, the intensity of (022) peak of CFA thin film increases with
103 increasing thickness of CFA thin film as shown in the top inset of Fig. 2(a), which indicates the
104 enhancement of crystallization. However, the position of (022) peak of CFA thin film remains
105 unchanged. According to the Scherrer Equation, grain sizes of CFA thin films were 28.6 nm, 29.7 nm,
106 31.1 nm, 31.8 nm and 34.2 nm with increasing thickness of CFA thin films, respectively, as shown in
107 Fig. 2(b), which is consistent with variation tendency of surface morphologies measured by SEM as
108 shown in the inset of Fig. 2(b). The increase of grain size with increasing thickness of CFA thin film
109 can indirectly influence the change of in-plane magnetic anisotropy field. The above results confirmed
110 the good quality of CFA/FGS structure we prepared, which have huge impact on the physical properties,
111 especially high-frequency magnetic properties.

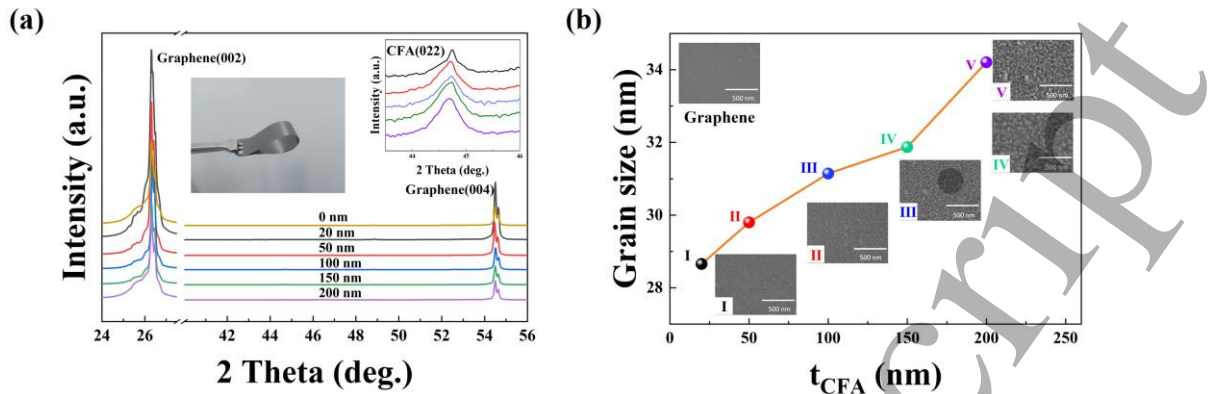


Fig. 2. (a) XRD patterns of CFA/FGS structure with different thicknesses of CFA thin film and (0 nm) pure graphene substrate. The inset shows digital photograph of FGS; (b) The grain size versus thickness of CFA thin film. The inset images show surface morphologies of CFA/FGS structure with different thicknesses and FGS.

The high-frequency magnetic properties of CFA thin films were measured by ferromagnetic resonance (FMR) using a vector network analyzer with coplanar waveguide method as shown in Fig. 3(a) and in the top inset of Fig. 3(c). In order to prove the good flexibility of graphene film and the stability of high frequency magnetic property of Co_2FeAl thin film grown on flexible graphene substrate, we choose the sample with 150-nm thick CFA thin film to fold over twenty cycles and then take FMR measurement at fixed 10 GHz every five cycles. The folding schematic diagram is shown in the bottom inset of Fig. 3(b). As shown in Fig. 3(b), the curves basically remain unchanged within twenty cycles. The resonance magnetic field approximately 800 Oe is obtained by fitting these curves according to Eq. (1). However, the dramatic change of the FMR curve occurs in folding twenty-fifth cycles. The shape of curve becomes slightly shaking and the curve deforms, which indicates the quality of CFA thin film deteriorates after being folded twenty cycles. The more cracks can be distinctly observed after twenty cycles as shown in the top inset of Fig. 3(b), which can be measured by RX50M Series Metallurgical Microscope. The similar result can be obtained for CFA thin film with 20 nm, 50 nm, 100 nm and 200 nm. Fig. 3(c) shows under different frequencies the typical FMR spectra for 150 nm-thick CFA thin film. In general, the magnetization is probed using a special phase correlation under the microwave excitation, and the FMR spectrum does not correspond to the imaginary part of the susceptibility alone, but in fact represents a mixture of the imaginary and real parts. Therefore, the actual function of the absorption curve can be fitted by an asymmetric Lorentzian function^[25]:

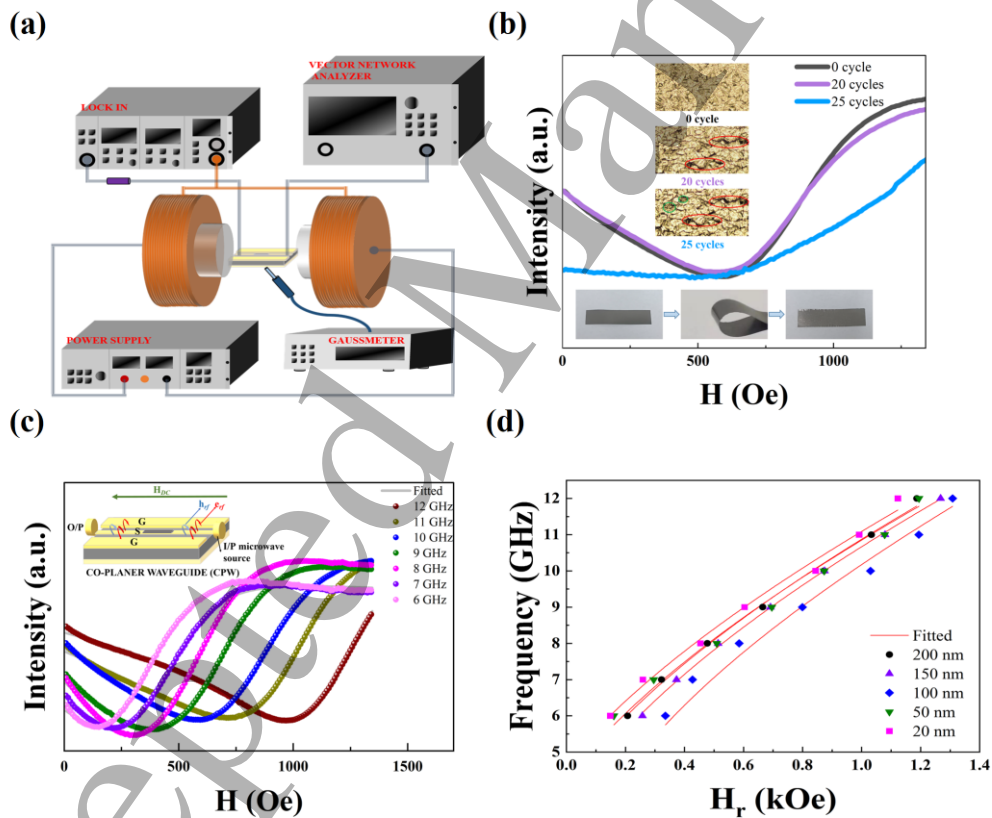
$$\varphi(H) = A \frac{\Delta H \cos \delta + (H - H_r) \sin \delta}{\Delta H^2 + (H - H_r)^2} \quad (1)$$

Where H is the external magnetic field, H_r is the magnetic resonance field, ΔH is the half-width at half-maximum of the linewidth, δ is the phase that mixes the real and imaginary parts of the dynamic susceptibility, and A is the integral coefficient. The fitting solid curve is shown in Fig. 3(c) in light gray color. The fitting result reveals that H_r shifts towards higher magnetic field with increasing frequency. For 150 nm-thick CFA thin film, the resonance magnetic field increase from 0.258 kOe to 1.268 kOe with the microwave frequency increasing from 6 GHz to 12 GHz as shown in Fig. 3(c). In addition,

142 frequency-dependent $\varphi(H)$ curves were measured for all thin film. As a result, the data of
 143 frequency-dependent H_r under different thicknesses of CFA thin film are shown in Fig. 3(d), which is
 144 fitted using the Kittel's equation.^[26]

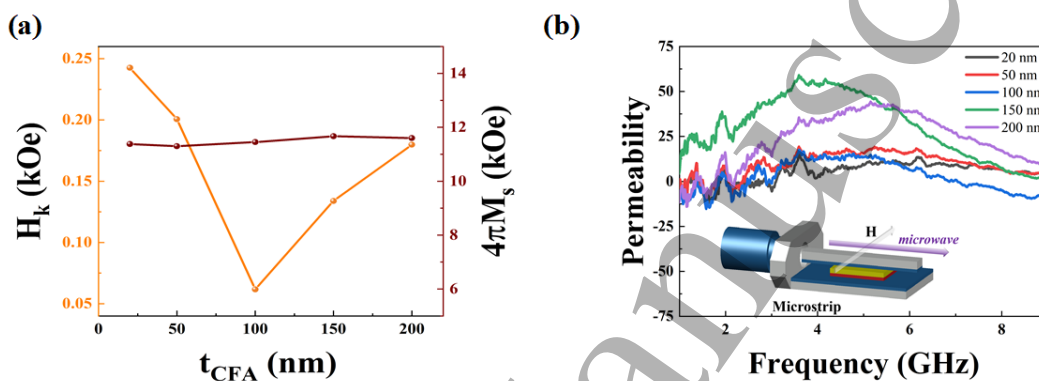
$$145 \quad f = \frac{\gamma}{2\pi} \sqrt{(H_r + H_k)(H_r + H_k + 4\pi M_s)} \quad (2)$$

146 Where gyromagnetic ratio $\gamma/2\pi=2.8$ GHz/kOe^[27,28], $4\pi M_s$ is the saturation magnetization, and H_k is the
 147 in-plane magnetic uniaxial anisotropy field. The data of frequency-dependent H_r was fitted using
 148 Equation (2) to extract $4\pi M_s$ and H_k . The fitting curve was shown in Fig. 3(d) with red color. With
 149 increasing thickness of CFA thin film, the value of $4\pi M_s$ is almost unchanged. However, H_k is found to
 150 decrease from 0.243 kOe to 0.062 kOe with increasing thickness from 20 nm to 100 nm as shown in
 151 Fig. 4(a). This can be explained as following: The crystallization of CFA thin film is enhanced with the
 152 increase of thickness of CFA thin film as shown in the inset of Fig. 2(b). Meanwhile, the grain size
 153 become larger. The competition between uniaxial magnetic anisotropy and magnetocrystalline
 154 anisotropy can appear, which can lead to the decrease of in-plane magnetic uniaxial anisotropy field.
 155 Nevertheless, H_k increases from 0.134 kOe to 0.180 kOe with thicknesses increasing from 150 nm to
 156 200 nm. The sudden increase in H_k for CFA thin film with 150 nm-thick can be attributed to releasing
 157 of substrate induced strain^[29], which can lead to the higher resonance frequency.



158
 159 **Fig. 3.** (a) The schematic illustration of ferromagnetic resonance (FMR) using a vector network analyzer; (b) These curves under
 160 unfolded state, and after being fold twenty cycles and twenty-fifth cycle. The top inset shows the more cracks with increasing
 161 folding cycles. The bottom inset shows the folding schematic diagram; (c) The experimental data (dots) and fitting curves (lines)
 162 of FMR for 150 nm-thick CFA thin film. The inset shows the device schematic of microstrip method; (d) The applied microwave
 163 frequency versus resonance magnetic field with different thicknesses of CFA thin film.

164 The dependence of permeability on the frequency with different thicknesses of CFA thin film was
 165 measured using a vector network analyzer with the microstrip method, as shown in the bottom inset of
 166 Fig. 4(b). When the thickness of CFA thin film less than 100 nm, there is no resonance peak detected in
 167 this method, which can be attributed to the disorderly arrangement of magnetic moment. This is related
 168 to roughness of surface morphologies. With continuing to increase the thickness of CFA thin film, the
 169 resonance peak can be obviously observed for CFA thin film with 150 nm and 200 nm-thick. The
 170 resonance frequency enhances from 3.4 GHz to 5.6 GHz, which is consistent with the result of H_k
 171 -dependent thickness of CFA thin film. Moreover, the resonance magnetic field and resonance
 172 frequency are quite stable though folded it over ten times, which demonstrates that good flexibility of
 173 graphene film and the ultrastability of high frequency property of CFA thin film grown on FGS.



174
 175 **Fig. 4.** (a) The change of H_k and $4\pi M_s$ with different thicknesses of CFA thin film; (b) The permeability spectra of CFA thin film.
 176 The inset shows the device schematic of coplanar waveguide method

178 4. Conclusion

179 In summary, we identified characteristics of CFA/FGS structure and high frequency magnetic property
 180 of CFA thin film with different thicknesses grown on FGS. With increasing thickness of CFA thin film,
 181 the surface becomes smoother, and grain size gradually increase, which can influence the change of
 182 in-plane magnetic anisotropy field. The in-plane magnetic anisotropy field gradually decreases when
 183 the thickness of CFA thin film increases from 20 nm to 100 nm by measurement of FMR. However,
 184 with thickness increasing to 100 nm, in-plane magnetic anisotropy field suddenly increases. The
 185 measurement result of the dependence of permeability on the frequency demonstrates that the
 186 resonance peak can be obviously observed at 3.4 GHz and 5.6 GHz with thickness 150 nm and 200 nm,
 187 which is in agreement with the result of FMR. Moreover, the high frequency parameter remains stable
 188 though folded it over twenty cycles, which indicates that good flexibility of graphene film and the
 189 ultrastability of high frequency property of CFA thin film grown on FGS. These results can be used to
 190 remove the obstacles that communication system transmission distance and signal quality.

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